

TM20G04NF

N+P-Channel Enhancement Mode Mosfet

General Description • Low $R_{DS(ON)}$ • RoHS and Halogen-Free Compliant Applications • Load switch • PWM	General Features N Channel $V_{DS} = 40V, I_D = 22A$ $R_{DS(ON)} = 17m\Omega @ V_{GS} = 10V$ P Channel $V_{DS} = -40V, I_D = -18A$ $R_{DS(ON)} = 33m\Omega @ V_{GS} = -10V$ 100% UIS Tested 100% R_g Tested																																																																			
D1 D1 D2 D2 S1 G1 S2 G2 D1 D2 D1 D2 S1 S2 G1 G2 Pin 1 NF:DFN5x6-8L Pin 1 Pin 1 D1 G1 S1 D2 G2 S2 Marking: 4020																																																																				
Absolute Maximum Ratings($T_A = 25^{\circ}C$ Unless Otherwise Noted) <table><tr><th rowspan="2">Symbol</th><th rowspan="2">Parameter</th><th colspan="2">Rating</th><th rowspan="2">Units</th></tr><tr><th>N-Channel</th><th>P-Channel</th></tr><tr><td>V_{DS}</td><td>Drain-Source Voltage</td><td>40</td><td>-40</td><td></td></tr><tr><td>V_{GS}</td><td>Gate-Source Voltage</td><td>± 20</td><td>± 20</td><td>V</td></tr><tr><td>$I_D @ T_A = 25^{\circ}C$</td><td>Continuous Drain Current, $V_{GS} @ 10V$</td><td>22</td><td>-18</td><td>A</td></tr><tr><td>$I_D @ T_A = 70^{\circ}C$</td><td>Continuous Drain Current, $V_{GS} @ 10V$</td><td>16</td><td>-14</td><td>A</td></tr><tr><td>I_{DM}</td><td>Pulsed Drain Current</td><td>68</td><td>-54</td><td>A</td></tr><tr><td>EAS</td><td>Single Pulse Avalanche Energy</td><td>19</td><td>27.5</td><td>mJ</td></tr><tr><td>$P_D @ T_C = 25^{\circ}C$</td><td>Total Power Dissipation</td><td>9.6</td><td>22</td><td>W</td></tr><tr><td>T_{STG}</td><td>Storage Temperature Range</td><td>-55 to 175</td><td>-55 to 175</td><td>$^{\circ}C$</td></tr><tr><td>T_J</td><td>Operating Junction Temperature Range</td><td>-55 to 175</td><td>-55 to 175</td><td>$^{\circ}C$</td></tr></table> Thermal Data <table><tr><th>Symbol</th><th>Parameter</th><th>Typ.</th><th>Max.</th><th>Unit</th></tr><tr><td>$R_{\theta JA}$</td><td>Thermal Resistance Junction-Ambient</td><td>---</td><td>75</td><td>$^{\circ}C/W$</td></tr><tr><td>$R_{\theta JC}$</td><td>Thermal Resistance Junction-Case</td><td>---</td><td>62.5</td><td>$^{\circ}C/W$</td></tr></table>		Symbol	Parameter	Rating		Units	N-Channel	P-Channel	V_{DS}	Drain-Source Voltage	40	-40		V_{GS}	Gate-Source Voltage	± 20	± 20	V	$I_D @ T_A = 25^{\circ}C$	Continuous Drain Current, $V_{GS} @ 10V$	22	-18	A	$I_D @ T_A = 70^{\circ}C$	Continuous Drain Current, $V_{GS} @ 10V$	16	-14	A	I_{DM}	Pulsed Drain Current	68	-54	A	EAS	Single Pulse Avalanche Energy	19	27.5	mJ	$P_D @ T_C = 25^{\circ}C$	Total Power Dissipation	9.6	22	W	T_{STG}	Storage Temperature Range	-55 to 175	-55 to 175	$^{\circ}C$	T_J	Operating Junction Temperature Range	-55 to 175	-55 to 175	$^{\circ}C$	Symbol	Parameter	Typ.	Max.	Unit	$R_{\theta JA}$	Thermal Resistance Junction-Ambient	---	75	$^{\circ}C/W$	$R_{\theta JC}$	Thermal Resistance Junction-Case	---	62.5	$^{\circ}C/W$
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N-Channel Electrical Characteristics (T_J=25°C unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	40	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =40V, V _{GS} =0V	-	-	1.0	μA
I _{GSS}	Gate to Body Leakage Current	V _{DS} =0V, V _{GS} =±20V	-	-	±100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	1.2	1.6	2.0	V
R _{DS(on)}	Static Drain-Source on-Resistance note3	V _{GS} =10V, I _D =8A	-	17	24	mΩ
		V _{GS} =4.5V, I _D =5A	-	25	35	mΩ
Dynamic Characteristics						
C _{iSS}	Input Capacitance	V _{DS} =20V, V _{GS} =0V, f=1.0MHz	-	633	-	pF
C _{oSS}	Output Capacitance		-	67	-	pF
C _{rSS}	Reverse Transfer Capacitance		-	58	-	pF
Q _g	Total Gate Charge	V _{DS} =20V, I _D =8A, V _{GS} =10V	-	12	-	nC
Q _{gs}	Gate-Source Charge		-	3.2	-	nC
Q _{gd}	Gate-Drain(“Miller”) Charge		-	3.1	-	nC
Switching Characteristics						
t _{d(on)}	Turn-on Delay Time	V _{DD} = 20V, R _L =2.5Ω V _{GS} =10V,R _{REN} =3Ω	-	4	-	ns
t _r	Turn-on Rise Time		-	3	-	ns
t _{d(off)}	Turn-off Delay Time		-	15	-	ns
t _f	Turn-off Fall Time		-	2	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I _S	Maximum Continuous Drain to Source Diode Forward Current		-	-	22	A
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	32	A
V _{SD}	Drain to Source Diode Forward Voltage	V _{GS} =0V, I _S = 8A	-	-	1.2	V

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P-Channel Electrical Characteristics (T_J=25°C unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D = -250μA	-40	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = -40V, V _{GS} =0V	-	-	-1	μA
I _{GSS}	Gate to Body Leakage Current	V _{DS} =0V, V _{GS} = ±20V	-	-	±100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D = -250μA	-1.0	-1.75	-2.5	V
R _{DS(on)}	Static Drain-Source on-Resistance note3	V _{GS} = -10V, I _D = -8A	-	33	38	mΩ
		V _{GS} = -4.5V, I _D = -5A	-	39	50	
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} = -20V, V _{GS} =0V, f=1.0MHz	-	1034	-	pF
C _{oss}	Output Capacitance		-	107	-	pF
C _{rss}	Reverse Transfer Capacitance		-	79.5	-	pF
Q _g	Total Gate Charge	V _{DS} = -20V, I _D = -8A, V _{GS} = -10V	-	20	-	nC
Q _{gs}	Gate-Source Charge		-	3.5	-	nC
Q _{gd}	Gate-Drain(“Miller”) Charge		-	4.2	-	nC
Switching Characteristics						
t _{d(on)}	Turn-on Delay Time	V _{DD} = -20V, I _D = -16A, V _{GS} = -10V, R _{GEN} =2.5Ω	-	8	-	ns
t _r	Turn-on Rise Time		-	15	-	ns
t _{d(off)}	Turn-off Delay Time		-	23	-	ns
t _f	Turn-off Fall Time		-	9	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I _S	Maximum Continuous Drain to Source Diode Forward Current		-	-	-18	A
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	-64	A
V _{SD}	Drain to Source Diode Forward Voltage	V _{GS} =0V, I _S = -16A	-	-0.8	-1.2	V
trr	Reverse Recovery Time	V _{GS} =0V, I _S =-16A,	-	29	-	ns
Qrr	Reverse Recovery Charge	di/dt=100A/μs	-	20	-	nC

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Typical Performance Characteristics-N

Figure1: Output Characteristics

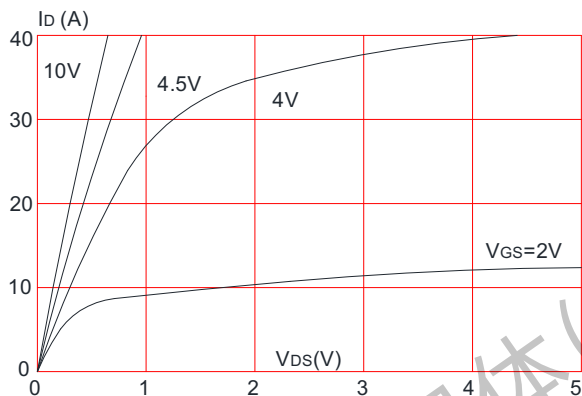


Figure 2: Typical Transfer Characteristics

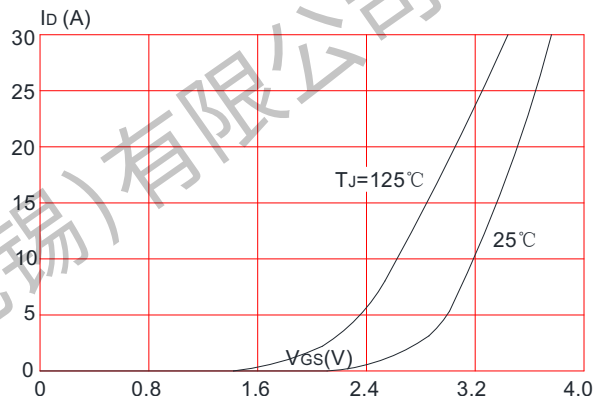


Figure 3: On-resistance vs. Drain Current

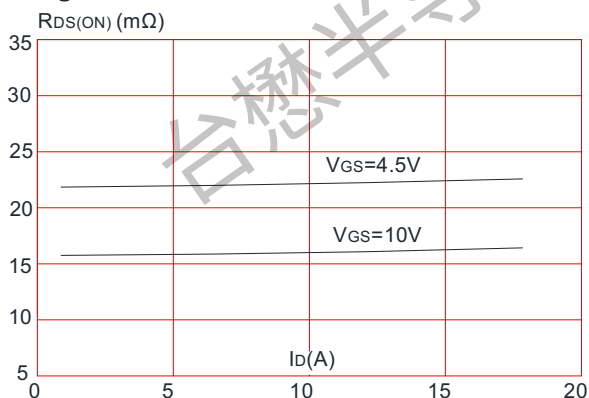


Figure 4: Body Diode Characteristics

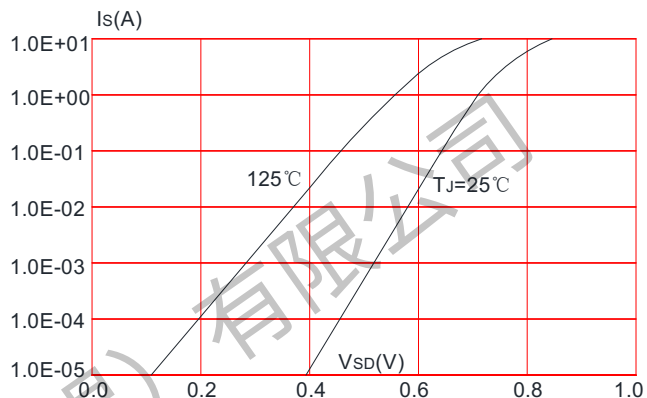


Figure 5: Gate Charge Characteristics

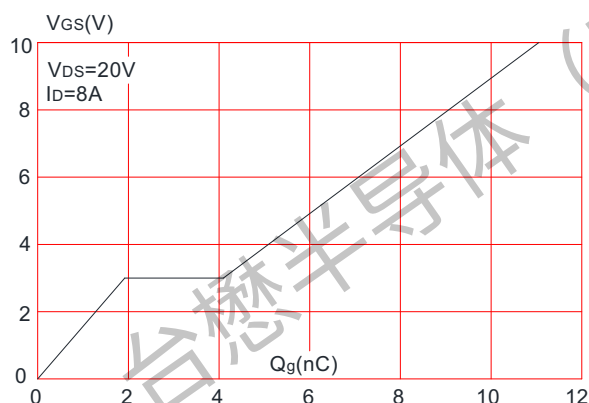
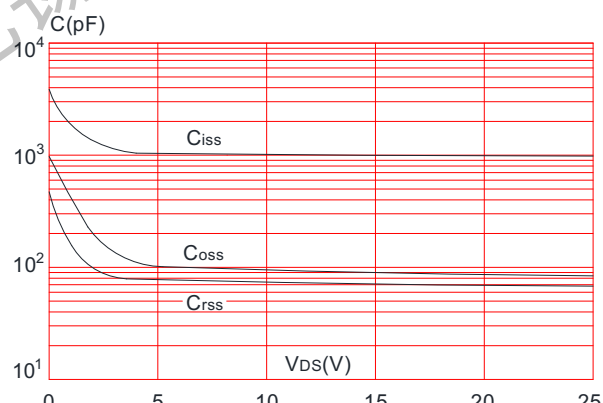


Figure 6: Capacitance Characteristics



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Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

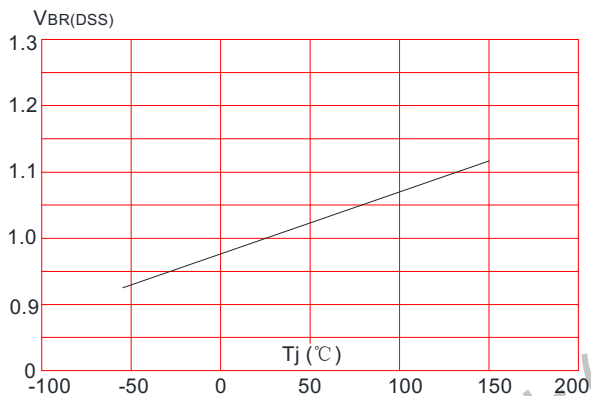


Figure 8: Normalized on Resistance vs. Junction Temperature

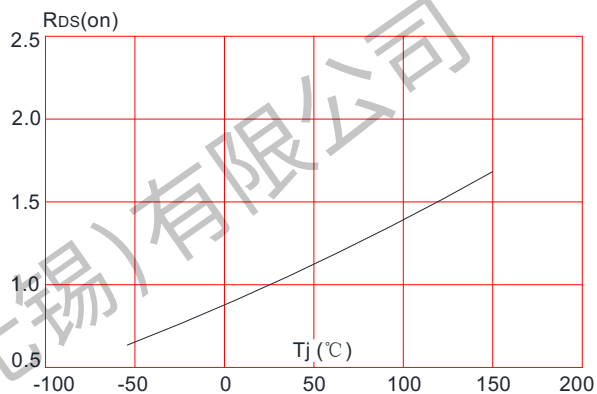


Figure 9: Maximum Safe Operating Area

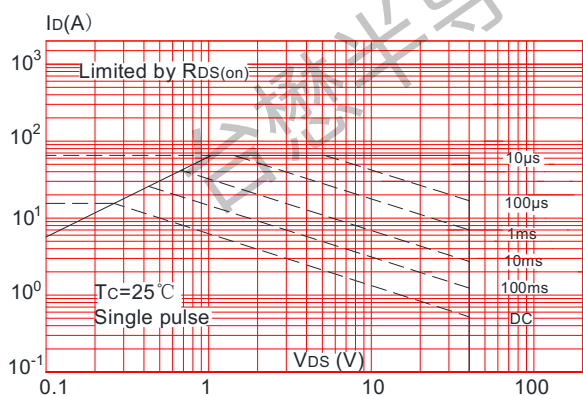
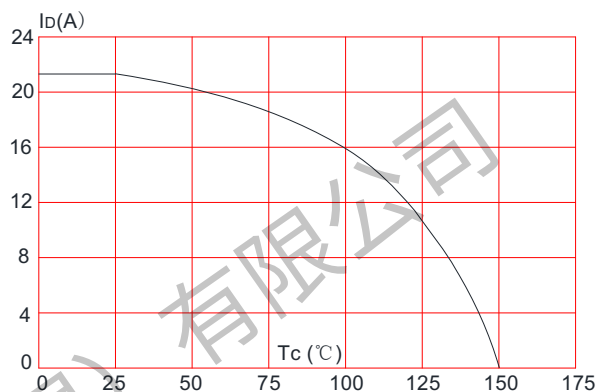
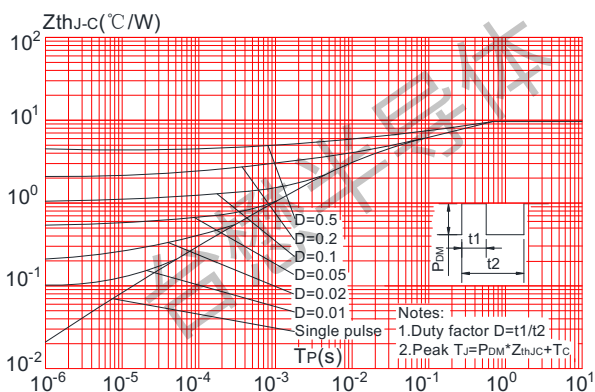


Figure 10: Maximum Continuous Drain Current vs. Case Temperature



Maximum Effective Transient Thermal Impedance, Junction-to-Case



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Typical Performance Characteristics-P

Figure 1: Output Characteristics

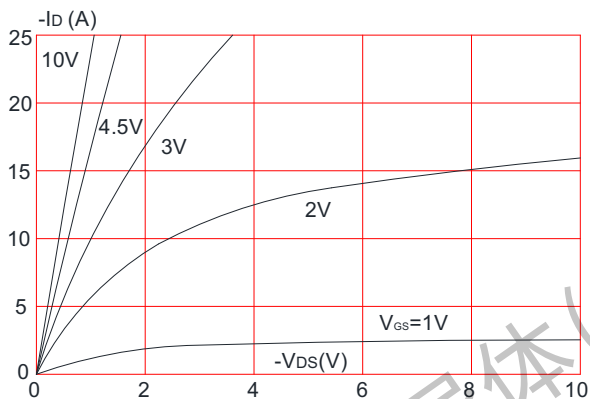


Figure 2: Typical Transfer Characteristics

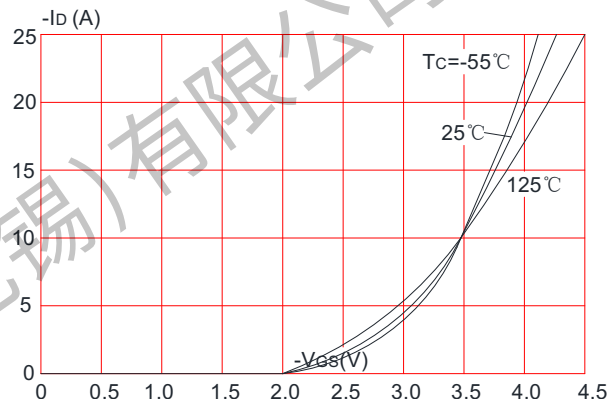


Figure 3: On-resistance vs. Drain Current

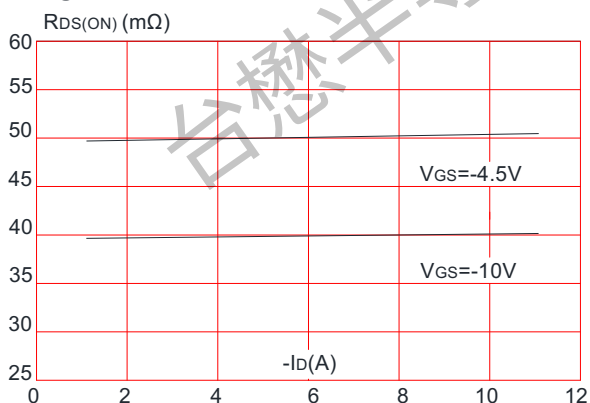


Figure 4: Body Diode Characteristics

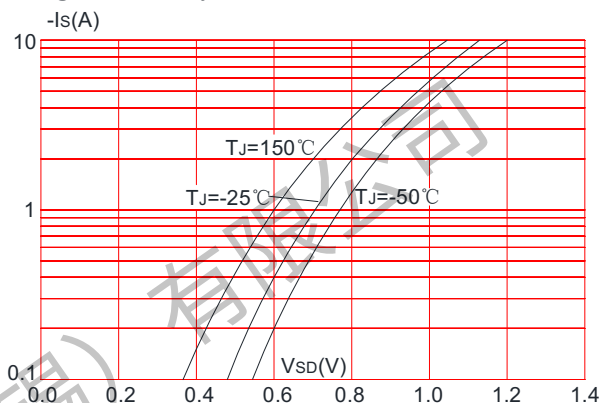


Figure 5: Gate Charge Characteristics

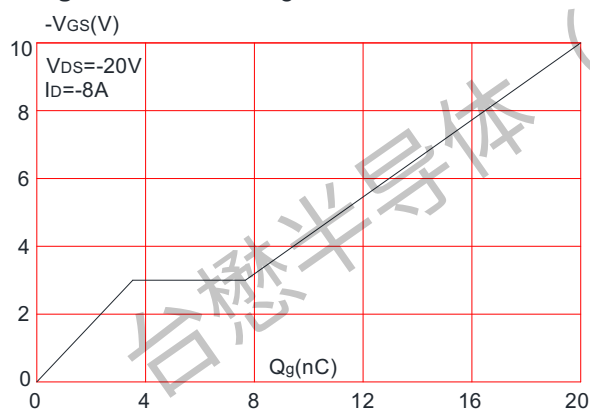
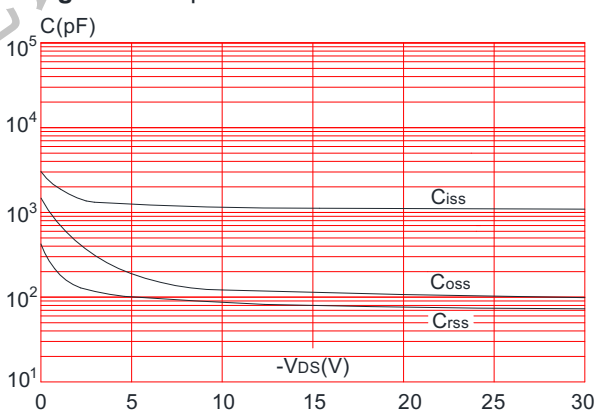


Figure 6: Capacitance Characteristics



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Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

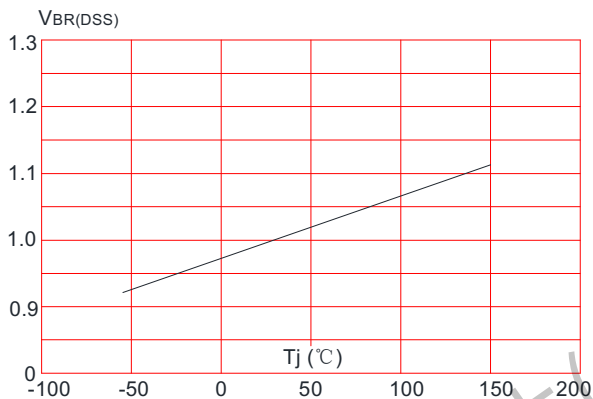


Figure 8: Normalized on Resistance vs. Junction Temperature

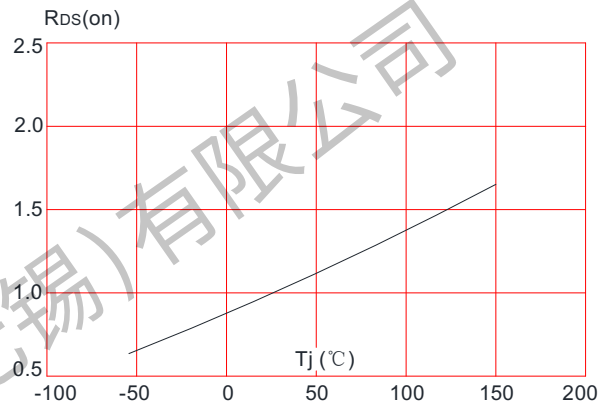


Figure 9: Maximum Safe Operating Area

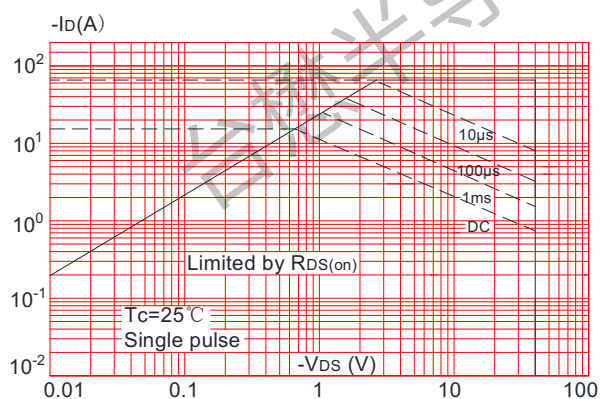


Figure 10: Maximum Continuous Drain Current vs. Case Temperature

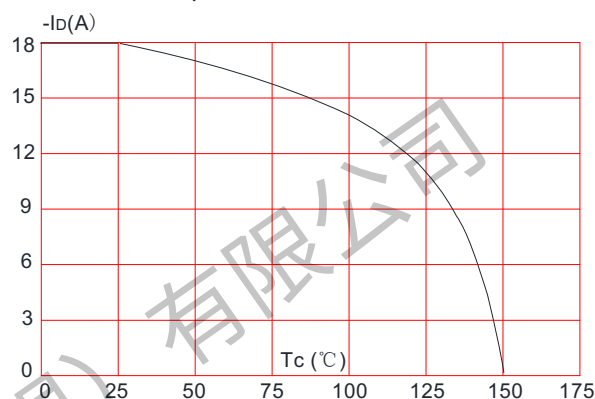
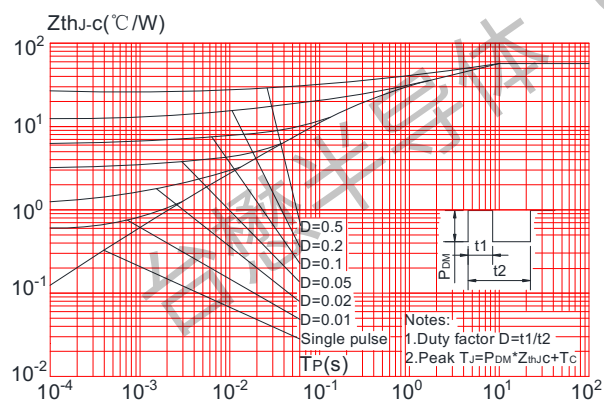


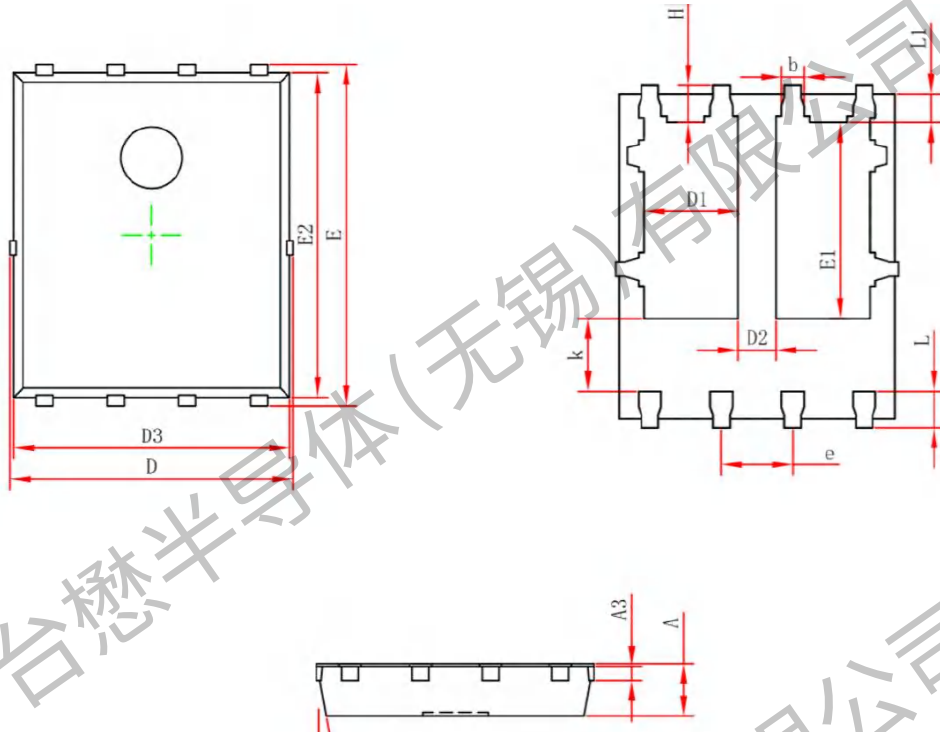
Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Case



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Package Mechanical Data:DFN5x6-8L

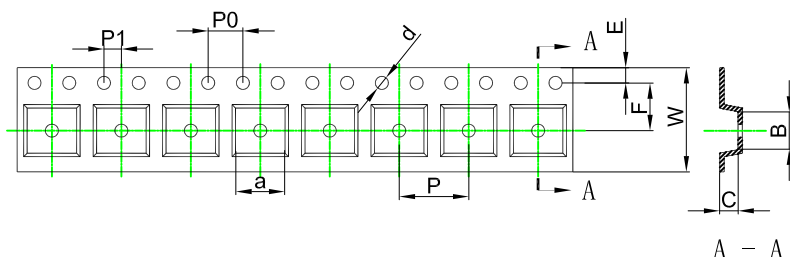


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.000	0.035	0.039
A3	0.154REF.		0.006REF.	
D	4.944	5.096	0.195	0.201
E	5.974	6.126	0.235	0.241
D1	1.470	1.870	0.058	0.074
D2	0.470	0.870	0.019	0.034
E1	3.375	3.575	0.133	0.141
D3	4.824	4.976	0.190	0.196
E2	5.674	5.826	0.223	0.229
k	1.190	1.390	0.047	0.055
b	0.350	0.450	0.014	0.018
e	1.270TYP.		0.050TYP.	
L	0.559	0.711	0.022	0.028
L1	0.424	0.576	0.017	0.023
H	0.574	0.726	0.023	0.029
θ	10°	12°	10°	12°

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PDFN5×6-8L Embossed Carrier Tape



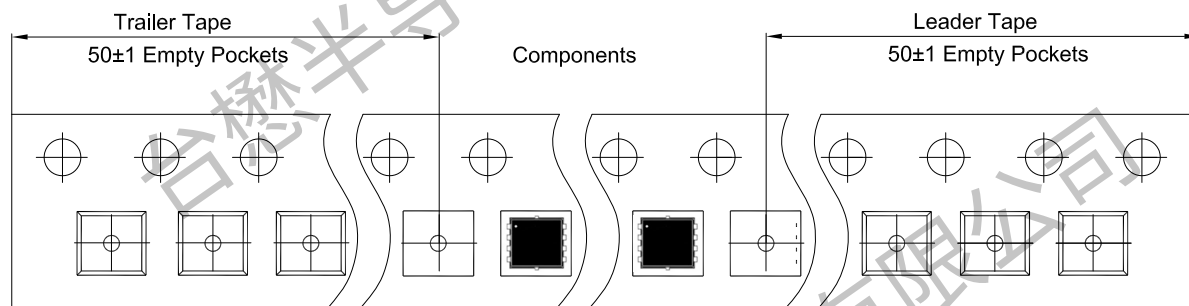
Packaging Description:

SOP-8L parts are shipped in tape. The carrier tape is made from a dissipative (carbon filled) polycarbonate resin. The cover tape is a multilayer film (Heat Activated Adhesive in nature) primarily composed of polyester film, adhesive layer, sealant, and anti-static sprayed agent. These reeled parts in standard option are shipped with 2,500 units per 13" or 33cm diameter reel. The reels are clear in color and is made of polystyrene plastic (anti-static coated).

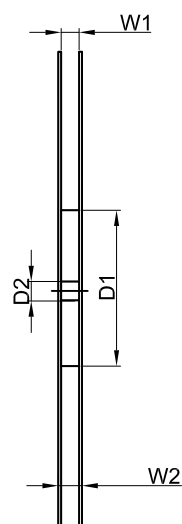
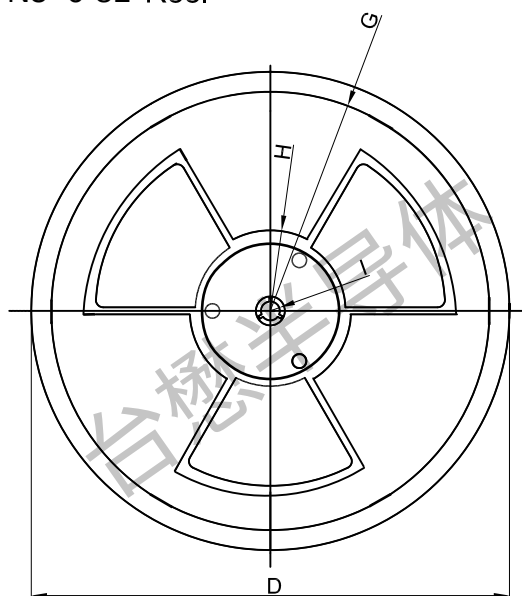
ALL DIM IN mm

Dimensions are in millimeter										
Pkg type	a	B	C	d	E	F	P0	P	P1	W
PDFN5×6-8L	6.40	5.40	2.10	Ø1.50	1.75	5.50	4.00	8.00	2.00	12.00

PDFN5×6-8L Tape Leader and Trailer



PDFN5×6-8L Reel



Dimensions are in millimeter								
Reel Option	D	D1	D2	G	H	I	W1	W2
13"Dia	Ø330.00	100.00	13.00	R135.00	R55.00	R6.50	12.00	14.00

REEL	Reel Size	Box	Box Size(mm)	Carton	Carton Size(mm)	G.W.(kg)
5,000 pcs	13 inch	10,000 pcs	370×355×52	50,000 pcs	400×360×368	

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Revision history:

Date	Rev	Description	Page
2023.12.09	23.12	Original	